RICOH |

R3154N Series

42 V Input Window Voltage Detector with Diagnostic Function for Automotive Applications

No. EC-528-200930

OVERVIEW

The R3154N is a Window Voltage Detector suitable for functional safety requirement. This device monitors over-and-under output voltages from the power supply IC for a microprocessor and a sensor, and detects abnormal voltage of systems. Its undervoltage detection down to 0.55 V is suitable for low power devices. Also, operation check of voltage detection is available with the TEST pin.

KEY BENEFITS

- Power supply from battery enables the voltage detector to operate independently from the power source.
- High-accuracy over-and-undervoltage detection from -1.25% to 0.75% and the hysteresis of Max. 0.75%.
- Overvoltage detection: 0.75 V at minimum, Undervoltage detection: 0.55 V at minimum.
- Compact package of SOT-23-6. Safe and secure adjacent pin configuration to prevent a short circuit.

KEY SPECIFICATIONS

- Operating Voltage Range (Max. Rating):
 3.0 V to 42.0 V (50.0 V)
- Operating Temperature Range: −40°C to 125°C
- Supply Current: Typ. 2.0 μA
- Overvoltage Detection: 0.75 V to 3.70 V (in 0.01 V step)
 Accuracy (V_{OVSET} > 0.9 V): ±0.5% (Ta = 25°C)

-1.25% to 0.75% (-40°C to 125°C)

- Undervoltage Detection: 0.55 V to 3.30 V (in 0.01 V step)
 Accuracy (V_{UVSET} > 0.66 V): ±0.5% (Ta = 25°C)
 -1.25% to 0.75% (-40°C to 125°C)
- Detection Release Hysteresis: Typ. 0.5%
- Detection Release Time: Typ. 20 μs
- Release Delay Time: Typ. 4 ms (C_D = 0.01 μF)
- Output Type: Nch. Open Drain

PACKAGE



SOT-23-6 2.9 x 2.8 x 1.1 (mm)

SELECTION GUIDE

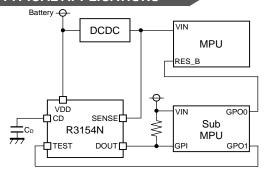
Product Name	Package	Quantity per Reel		
R3154NxxxA-TR-##	SOT-23-6	3,000 pcs		

xxx: The combination of an overvoltage detection setting voltage (V_{OVSET}) and an undervoltage detection setting voltage (V_{UVSET})

Refer to *Product-specific Electrical Characteristics* for details.

#: Quality Class Refer to SELECTION GUIDE for details.

TYPICAL APPLICATIONS



C_D: a capacitor corresponding to the set release delay time

APPLICATIONS

- Power supply voltage monitoring for systems which require fault detection, such as ECU and ADAS.
- Power supply voltage monitoring for control units such as EV inverters and Charge Controllers.

SELECTION GUIDE

The detection setting voltages and quality class are user-selectable.

Selection Guide

Product Name	Product Name Package		Pb Free	Halogen Free	
R3154NxxxA-TR-##	SOT-23-6	3,000 pcs	Yes	Yes	

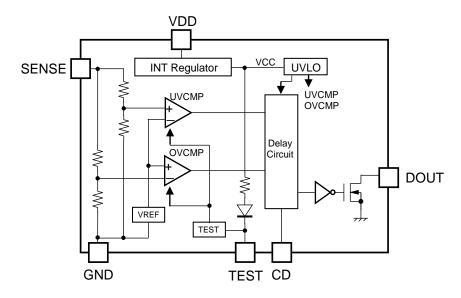
xxx: The combination of an overvoltage detection setting voltage (Vovset) and an undervoltage detection setting voltage (Vuvset).

Refer to Product-specific Electrical Characteristics for details.

#: Quality Class

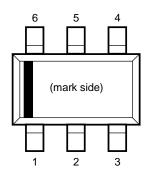
Quality Class	##	Operating Temperature Range	Test Temperature
Α	AE	-40°C to 125°C	25°C, High
R	R	−40°C to 125°C	Low, 25°C, High

BLOCK DIAGRAM



R3154N Block Diagram

PIN DESCRIPTIONS



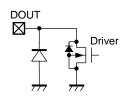
SOT-23-6 Pin Configuration

Pin Descriptions

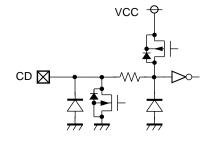
Pin No.	Symbol	Description
1	VDD	Supply Voltage Pin
2	CD	Release Delay Time Set Pin ("Open" when not connected)
3	DOUT	Voltage Fault Detection Output Pin ("Low" at detection)
4	TEST	TEST Pin ("Low" at operation check of voltage detection)
5	GND	GND Pin
6	SENSE	SENSE Voltage Input Pin

Internal Equivalent Circuit for Each Pin

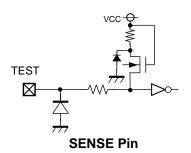


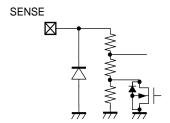


CD Pin



TEST Pin





ABSOLUTE MAXIMUM RATINGS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
M	Supply Voltage	-0.3 to 50.0	V
V_{DD}	Peak Voltage ⁽¹⁾	60	V
Vcd	CD Pin Output Voltage	-0.3 to 20.0	V
V _{DOUT}	DOUT Pin Output Voltage	-0.3 to 20.0	V
V _{TEST}	TEST Pin Voltage	-0.3 to 20.0	V
Vsense	SENSE Pin Voltage	-0.3 to 20.0	V
Іроит	DOUT Pin Output Current	30	mA
P _D	Power Dissipation	Refer to Appe	
Tj	Junction Temperature Range	-40 to 150	°C
Tstg	Storage Temperature Range	-55 to 150	°C

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITIONS

Recommended Operating Conditions

Symbol	Parameter	Rating	Unit
V_{DD}	Operating Voltage	3.0 to 42	V
V _{SENSE}	SENSE Input Voltage	0 to 6.0	V
V _{TEST}	TEST Pin Voltage	0 to 6.0	V
V _{UP}	DOUT Pin Pull-up Voltage	0 to 6.0	V
Та	Operating Temperature Range	-40 to 125	°C

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such ratings by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

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⁽¹⁾ Duration Time: Within 200 ms

ELECTRICAL CHARACTERISTICS

 $V_{DD} = 14 \text{ V}, C_D = 0.01 \ \mu\text{F}, \text{ pulled-up to 5 V with 100 k}\Omega, \text{ unless otherwise specified.}$ The specifications surrounded by are guaranteed by design engineering at -40°C \leq Ta \leq 125°C.

R3154N (-AE) Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Symbol	Parameter	Test Condi	tions	Min.	Тур.	Max.	Unit
		T- 25%C	0.9 V < V _{OVSET}	x0.995		x1.005	V
V	Overvoltage (OV)	Ta = 25°C	V _{OVSET} ≤ 0.9 V	-4.5		+4.5	mV
VOVDET	Detector Threshold	–40°C ≤ Ta ≤ 125°C	0.9 V < Vovset	x0.9875		x1.0075	V
		-40 C ≤ Ta ≤ 125 C	V _{OVSET} ≤ 0.9 V	-11.25		+6.75	mV
		Ta = 25°C	0.66V < VUVSET	x0.995		x1.005	٧
V _{UVDET}	Undervoltage (UV)	Ta = 25 C	V _{UVSET} ≤ 0.66V	-3.3		+3.3	mV
V UVDE I	Detector Threshold	–40°C ≤ Ta ≤ 125°C	0.66 V< V _{UVSET}	x0.9875		x1.0075	>
		-40 C \$ 1a \$ 125 C	V _{UVSET} ≤ 0.66V	-8.25		+4.95	mV
Voveys	Overvoltage (OV) Threshold Hysteresis			V _{OVDET} ×0.0025	V _{OVDET} ×0.005	V _{OVDET} ×0.0075	٧
Vuvhys	Undervoltage (UV) Threshold Hysteresis			V _{UVDET} ×0.0025	$V_{UVDET} \times 0.005$	V _{UVDET} ×0.0075	٧
Iss	Supply Current	V _{UVDET} < V _{SENSE} < V _O	VDET		2.0	5.0	μΑ
Rsense	SENSE Pin Resistance ⁽¹⁾	Resistance between S	ENSE and GND	3		32	ΜΩ
V _{UVLO}	UVLO Detector Threshold				1.8	2.7	V
Vuvlohys	UVLO Threshold Hysteresis				0.1	0.3	V
V_{DDL}	DOUT Pin Output Low-operating Voltage ⁽²⁾					1.7	V
Гоит	NMOS Driver Output Current	$V_{DD} = 3.0, V_{DS} = 0.1$	V	0.37	0.75		mA
I _{LEAK}	NMOS Driver Leakage Current	V _{DOUT} = 5.5 V			0	1	μΑ
V _{TESTH}	TEST Pin Input Voltage, "High"			1.6			>
VTESTL	TEST Pin Input Voltage, "Low"					0.5	V
t _{DELAY}	Release Delay Time			2.5	4	8	ms

All test items listed in Electrical Characteristics are done under the pulse load condition (Tj \approx Ta = 25°C)

 $^{^{(2)}}$ Minimum value of power supply voltage when an output voltage becomes 0.1V or less at detection. (Pulled-up resistance: 100 k Ω , Pulled-up voltage: 5 V)



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⁽¹⁾ Typ. value varies depending on the set value of detector threshold.

 V_{DD} = 14 V, C_D = 0.01 μF , pulled-up to 5 V with 100 $k\Omega$, unless otherwise specified.

R3154N (-R) Electrical Characteristics

(-40°C ≤ Ta ≤ 125°C)

Symbol	Parameter	Test Condi	tions	Min.	Тур.	Max.	Unit
		T- 0500	0.9 V < V _{OVSET}	x0.995		x1.005	V
V	Overvoltage (OV)	Ta = 25°C	V _{OVSET} ≤ 0.9 V	-4.5		+4.5	mV
VOVDET	Detector Threshold	–40°C ≤ Ta ≤ 125°C	0.9 V < Vovset	x0.9875		x1.0075	V
		-40 C ≤ Ta ≤ 125 C	V _{OVSET} ≤ 0.9 V	-11.25		+6.75	mV
		Ta = 25°C	0.66V < VUVSET	x0.995		x1.005	V
Vuvdet	Undervoltage (UV)	1a = 25 C	V _{UVSET} ≤ 0.66V	-3.3		+3.3	mV
VUVDET	Detector Threshold	–40°C ≤ Ta ≤ 125°C	0.66 V< V _{UVSET}	x0.9875		x1.0075	V
		-40 C 3 Ta 3 125 C	V _{UVSET} ≤ 0.66V	-8.25		+4.95	mV
Vovhys	Overvoltage (OV) Threshold Hysteresis			V _{OVDET} ×0.0025	$V_{OVDET} \times 0.005$	V _{OVDET} ×0.0075	V
Vuvhys	Undervoltage (UV) Threshold Hysteresis			V _{UVDET} ×0.0025	V _{UVDET} ×0.005	V _{UVDET} ×0.0075	٧
Iss	Supply Current	V _{UVDET} < V _{SENSE} < V _O	VDET		2.0	5.0	μΑ
RSENSE	SENSE Pin Resistance ⁽¹⁾	Resistance between S	ENSE and GND	3		32	МΩ
V _{UVLO}	UVLO Detector Threshold				1.8	2.7	V
Vuvlohys	UVLO Threshold Hysteresis				0.1	0.3	V
V_{DDL}	DOUT Pin Output Low-operating Voltage ⁽²⁾					1.7	V
I _{OUT}	NMOS Driver Output Current	$V_{DD} = 3.0, V_{DS} = 0.1$	V	0.37	0.75		mA
I _{LEAK}	NMOS Driver Leakage Current	V _{DOUT} = 5.5 V			0	1	μΑ
V_{TESTH}	TEST Pin Input Voltage, "High"			1.6			>
V _{TESTL}	TEST Pin Input Voltage, "Low"					0.5	V
t _{DELAY}	Release Delay Time			2.5	4	8	ms

⁽²⁾ Minimum value of power supply voltage when an output voltage becomes 0.1V or less at detection. (Pulled-up resistance: $100 \text{ k}\Omega$, Pulled-up voltage: 5 V)



⁽¹⁾ Typ. value varies depending on the set value of detector threshold.

 $V_{DD}=14$ V, $C_D=0.01~\mu F,$ pulled-up to 5 V with 100 $k\Omega,$ unless otherwise specfied.

The specifications surrounded by are guaranteed by design engineering at $-40^{\circ}\text{C} \le \text{Ta} \le 125^{\circ}\text{C}$.

R3154N-AE Product-specific Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Product	Vo	VDET (V))	V _{UVDET} (V)			
name	Min.	Тур.	Max.	Min.	Тур.	Max.	
R3154N201A	0.85550	0.86	0.86450	0.76615	0.77	0.77385	
R3154N202A	0.74550	0.75	0.75450	0.54670	0.55	0.55330	
R3154N203A	3.52230	3.54	3.55770	3.03475	3.05	3.06525	
R3154N204A	1.32335	1.33	1.33665	1.16415	1.17	1.17585	
R3154N205A	1.07460	1.08	1.08540	0.91540	0.92	0.92460	
R3154N206A	0.86550	0.87	0.87450	0.72635	0.73	0.73365	

(-40°C ≤ Ta ≤ 125°C)

Product	V _{OVDET} (V)			V _{UVDET} (V)			Vovers (V)			Vuvhys (V)		
name	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.
R3154N201A	0.84875	0.86	0.86675	0.76038	0.77	0.77577	0.00215	0.00430	0.00645	0.00193	0.00385	0.00577
R3154N202A	0.73875	0.75	0.75675	0.54175	0.55	0.55495	0.00188	0.00375	0.00562	0.00138	0.00275	0.00412
R3154N203A	3.49575	3.54	3.56655	3.01188	3.05	3.07287	0.00885	0.01770	0.02655	0.00763	0.01525	0.02287
R3154N204A	1.31338	1.33	1.33997	1.15538	1.17	1.17877	0.00333	0.00665	0.00997	0.00293	0.00585	0.00877
R3154N205A	1.06650	1.08	1.08810	0.90850	0.92	0.92690	0.00270	0.00540	0.00810	0.00230	0.00460	0.00690
R3154N206A	0.85875	0.87	0.87675	0.72088	0.73	0.73547	0.00218	0.00435	0.00652	0.00183	0.00365	0.00547

R3154N-R Product-specific Electrical Characteristics

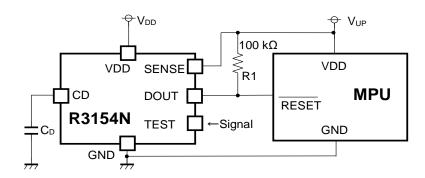
 $(Ta = 25^{\circ}C)$

Product	Vo	VDET (V))	V _{UVDET} (V)					
name	Min.	Тур.	Max.	Min.	Тур.	Max.			
R3154N201A	0.85550	0.86	0.86450	0.76615	0.77	0.77385			
R3154N202A	0.74550	0.75	0.75450	0.54670	0.55	0.55330			
R3154N203A	3.52230	3.54	3.55770	3.03475	3.05	3.06525			
R3154N204A	1.32335	1.33	1.33665	1.16415	1.17	1.17585			
R3154N205A	1.07460	1.08	1.08540	0.91540	0.92	0.92460			
R3154N206A	0.86550	0.87	0.87450	0.72635	0.73	0.73365			

 $(-40^{\circ}C \le Ta \le 125^{\circ}C)$

Product	V _{OVDET} (V)			V _{UVDET} (V)			Vovers (V)			Vuvhys (V)		
name	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.
R3154N201A	0.84875	0.86	0.86675	0.76038	0.77	0.77577	0.00215	0.00430	0.00645	0.00193	0.00385	0.00577
R3154N202A	0.73875	0.75	0.75675	0.54175	0.55	0.55495	0.00188	0.00375	0.00562	0.00138	0.00275	0.00412
R3154N203A	3.49575	3.54	3.56655	3.01188	3.05	3.07287	0.00885	0.01770	0.02655	0.00763	0.01525	0.02287
R3154N204A	1.31338	1.33	1.33997	1.15538	1.17	1.17877	0.00333	0.00665	0.00997	0.00293	0.00585	0.00877
R3154N205A	1.06650	1.08	1.08810	0.90850	0.92	0.92690	0.00270	0.00540	0.00810	0.00230	0.00460	0.00690
R3154N206A	0.85875	0.87	0.87675	0.72088	0.73	0.73547	0.00218	0.00435	0.00652	0.00183	0.00365	0.00547

TYPICAL APPLICATION CIRCUIT

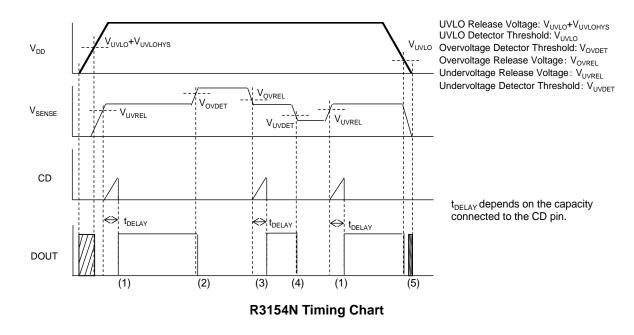


R3154N Typical Application Circuit

Recommended External Components

Symbol	Description		
	A capacitor should be selected corresponding to the set Release Delay Time. Refer to		
С	"Delay in Operation and Release Delay Time (tDELAY)" in THEORY OF OPERATION for details.		
	When minimizing the release delay time, layout the circuit without any capacitor.		
R1	The "Low" voltage of the DOUT output is determined by the division ratio of the on resistance		
	of the NMOS driver and the pull-up resistance value (R1). The on-resistance of the NMOS		
	driver is calculated from the "NMOS driver output current". Select the pull-up resistance value		
	(R1) to bring the "Low" voltage of the DOUT output to the desired voltage.		
	The "High" level of the DOUT output is determined by the division ratio of the leakage current		
	of the NMOS driver and the pull-up resistance value (R1).		
	The leakage current of the NMOS driver is calculated from the "NMOS driver leakage current".		
	Confirm if the "High" voltage of the DOUT output is the desired voltage.		
	"Electrical Characteristic" is evaluated in conditions that pull-up voltage = 5 V and R1 = 100 k Ω .		

THEORY OF OPERATION

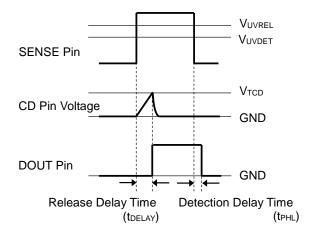


- (1) When the SENSE pin voltage (V_{SENSE}) exceeds the undervoltage release voltage (V_{UVREL}), the DOUT pin outputs "High" after the release delay time (t_{DELAY}).
- (2) When V_{SENSE} exceeds the overvoltage detector threshold (V_{OV DET}) by increasing of the voltage, the DOUT pin outputs "Low" after the detection delay time (Typ. 20 μs) and this triggers the overvoltage detecting state.
- (3) When V_{SENSE} decreases less than the overvoltage release voltage (V_{OVREL}), the DOUT pin outputs "High" after the release delay time (t_{DELAY}).
- (4) When V_{SENSE} decreases less than the undervoltage detector threshold (V_{UVDET}), the DOUT pin outputs "Low" after the detection delay time (Typ. 20 μs) and this triggers the undervoltage detecting state.
- (5) When the VDD pin voltage (V_{DD}) decreases less than the UVLO detector threshold (V_{UVLO}), the DOUT pin outputs "Low". Note that DOUT cannot maintain "Low" when the VDD pin voltage drops further and becomes lower than V_{DDL}.

Delay Operation and Release Delay Time (tDELAY)

At Undervoltage Detection

A higher voltage than the undervoltage release voltage (V_{UVREL}) supplied to the SENSE pin triggers charging of the external capacitor (C_D capacitance), then the CD pin voltage (V_{CD}) increases. The DOUT pin voltage (V_{DOUT}) maintains "Low" until V_{CD} reaches the CD pin threshold voltage (V_{TCD}). When V_{CD} exceeds V_{TCD} , V_{DOUT} transitions from "Low" to "High". The release delay time (t_{DELAY}) is the period from the time the SENSE pin voltage (V_{SENSE}) exceeds V_{UVREL} to a rising edge of V_{DOUT} . V_{DOUT} transitions from "Low" to "High" and it leads to discharging of the C_D capacitor. Without the C_D capacitor, it becomes the short t_{DELAY} (Typ. 20 μ s) depending on the circuit delay and CD pin stray capacity. When the higher voltage than V_{UVDET} is supplied to the SENSE pin, the detection delay time (t_{PHL}), which is the period that V_{DOUT} transitions from "High" to "Low", remains constant regardless of the capacitance value of the external capacitor.



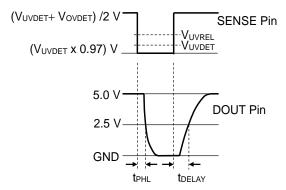
Undervoltage Release Delay Timing Chart

Calculation of Release Delay Time (t_{DELAY}) at Undervoltage Detection

The typical value of the release delay time (t_{DELAY}) with the capacitance of the external capacitor (C_D) is calculated in the following equation:

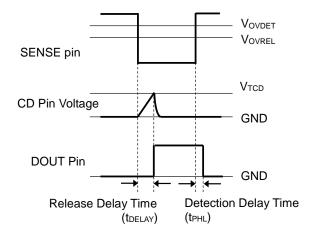
$$t_{DELAY}(s) = 0.73 \times C_D(F) / (1.8 \times 10^{-6})$$

 t_{DELAYn} is the period until the DOUT pin voltage reaches 2.5 V after the pulse voltage of (VUVDET + VOVDET) /2 V increased from (VUVDET x 0.97) V is supplied to the SENSE pin when DOUT pin is pulled up to 5 V with 100 k Ω .



At Overvoltage Detection

A lower voltage than the overvoltage release voltage (Vovrel) supplied to the SENSE pin triggers charging of the external capacitor (CD capacitance), then the CD pin voltage (VCD) increases. The DOUT pin voltage (VDOUT) maintains "Low" until VCD reaches the CD pin threshold voltage (VTCD). When VCD exceeds VTCD, VDOUT is inverted from "Low" to "High". The release delay time (tDELAY) is the period from the time the SENSE pin voltage (VSENSE) falls below VOVREL to a rising edge of VDOUT. VDOUT transitions to "High". VDOUT transitions from "Low" to "High" and it leads to discharging of the CD capacitor. Without the CD capacitor, it becomes the short tDELAY (Typ. 20 µs) depending on the circuit delay and CD pin stray capacity. When the higher voltage than VOVDET is supplied to the SENSE pin, the detection delay time (tPHL), which is the period that VDOUT transitions from "High" to "Low", remains constant regardless of the capacitance value of the external capacitor.



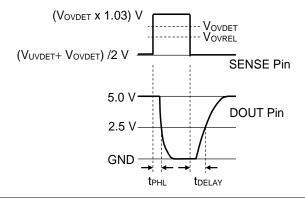
Overvoltage Release Delay Timing Chart

Calculation of Release Delay Time (t_{DELAY}) at Overvoltage Detection

The typical value of the release delay time (t_{DELAY}) with the capacitance of the external capacitor (C_D) is calculated in the following equation:

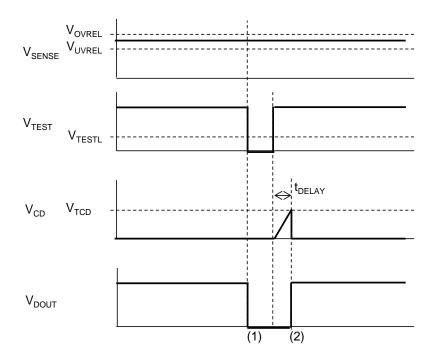
$$t_{DELAY}(s) = 0.73 \times C_D(F) / (1.8 \times 10^{-6})$$

 t_{DELAY} is the period until the DOUT pin voltage reaches 2.5 V after the pulse voltage of $(V_{UVDET} + V_{OVDET})$ /2 V decreased from $(V_{OVDET} \times 1.03)$ V is supplied to the SENSE pin when DOUT pin is pulled up to 5 V with 100 k Ω .



Operation Check of Voltage Detection Function with TEST Pin

Voltage Detection Function is to set DOUT to "Low" by inputting "Low" to the TEST pin, even when the SENSE pin voltage (V_{SENSE}) is within a range of the release voltage. If the DOUT does not become "Low" even V_{SENSE} is within the release voltage range and "Low" signal is input to the TEST pin, it can be judged that the IC has a fault. To cancel this function, set the TEST pin to "High" voltage or "Open". When the TEST pin is open, the DOUT becomes "High" with pulled-up voltage in the IC.



TEST Pin Timing Chart

- (1) When inputting "Low" to the TEST pin, the DOUT is fixed to "Low" after the detection delay time (Typ. 20 μ s) even if the SENSE pin voltage (V_{SENSE}) is within a range of the release voltage. The "Low" signal of TEST pin voltage should be 50 μ s or more.
- (2) When the TEST pin transitions from "Low" to "High", the DOUT pin outputs "High" after the release delay time (t_{DELAY}). At this time, the TEST pin should maintain "High" for the release delay time or longer. Even when the external capacitor (C_D capacitance) is not connected, it should maintain "High" for 50 µs or more.

■ APPLICATION INFORMATION

The concept of "H" level of TEST pin

The R3154 has a voltage regulator (INT regulator) inside the IC. Major functions of the IC are operated by VCC (Typ. 3.3V) generated by INT regulator from input voltage, VDD.

TEST pin is pulled up to VCC voltage via 100kΩ as it can be set to open when TEST pin is unused.

When the voltage detect function is in use, when input "Low" voltage to TEST pin, then DOUT pin becomes "Low". But when the voltage detect function is in no use, if "High" voltage is input to TEST pin, the current which is determined by the following equation flows continuously. This makes the supply current increase.

$$(VCC - TEST "High" voltage) /100kΩ$$
 (VCC>TEST "High" voltage)

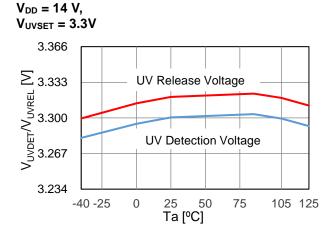
Unless there's a specific reason to avoid an OPEN pin condition, it's recommended to be left OPEN when TEST pin is not used.

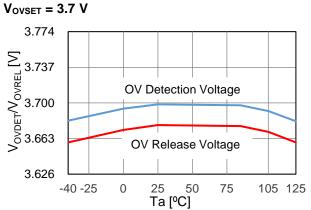
As the circuit configuration prevents a reverse current from TEST pin to VCC, even when being used in condition of TEST "High" voltage > VCC, supply current doesn't increase and VCC voltage doesn't vary.

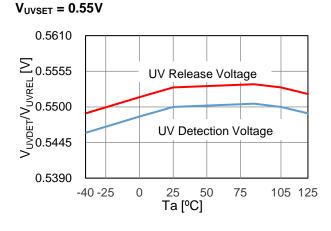
■ TYPICAL CHARACTERISTICS

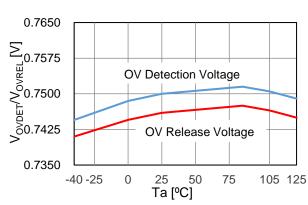
Note: Typical Characteristics are intended to be used as reference data; they are not guaranteed.

1) UV/OV Detection Release Voltage vs. Temperature



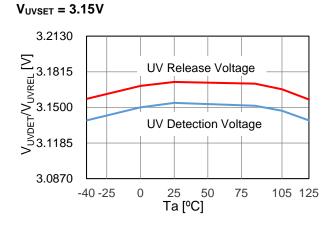


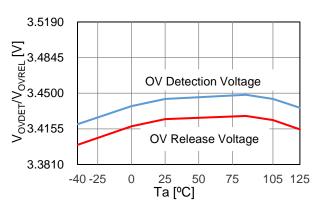




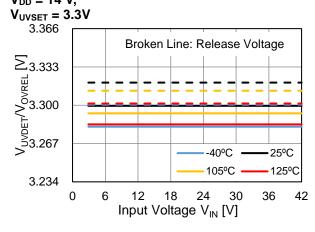
 $V_{OVSET} = 0.75 V$

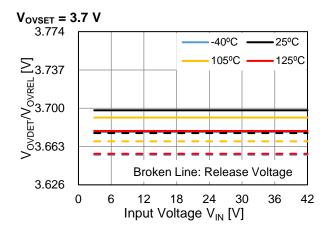
V_{OVSET} = 3.45 V

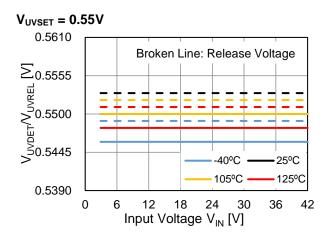


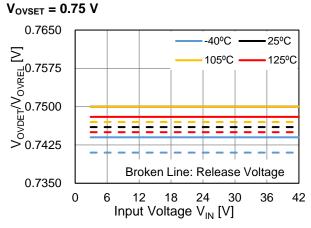


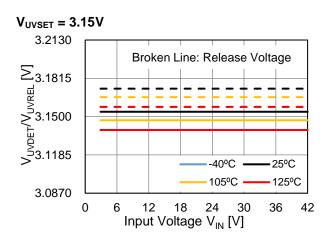
2) UV/OV Detection Voltage vs. Input Voltage $V_{DD} = 14 \text{ V}$,

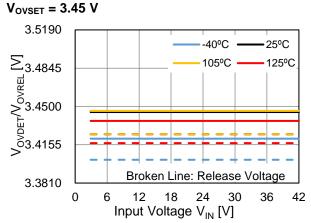






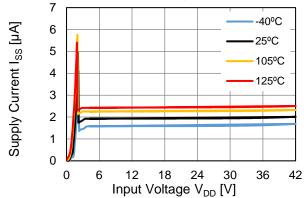




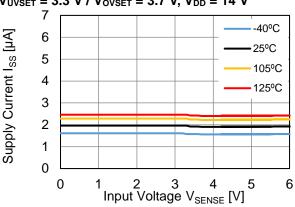


3) Supply Current vs. Input Voltage

V_{UVSET} = 3.3 V / V_{OVSET} = 3.7 V, V_{SENSE} = 3.5V

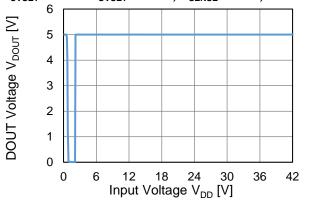


4) Supply Current vs. V_{SENSE} V_{UVSET} = 3.3 V / V_{OVSET} = 3.7 V, V_{DD} = 14 V



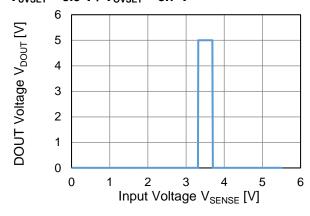
5) DOUT Pin Voltage vs. Input Voltage

 $V_{UVSET} = 3.3 \text{ V/V}_{OVSET} = 3.7 \text{ V}, V_{SENSE} = 3.5 \text{V}, Ta = 25^{\circ}\text{C}$

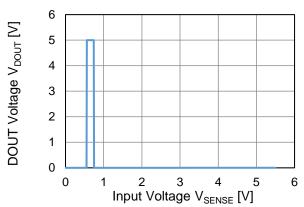


6) DOUT Pin Voltage vs. V_{SENSE} V_{DD} = 14 V, Ta = 25°C,

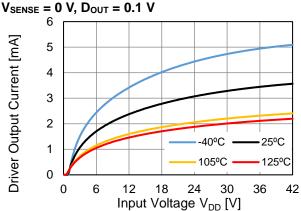
 $V_{UVSET} = 3.3 \text{ V} / V_{OVSET} = 3.7 \text{ V}$



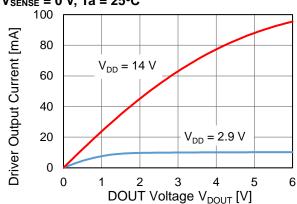
$$V_{\text{UVSET}} = 0.55 \text{ V} / V_{\text{OVSET}} = 0.75 \text{ V}$$



7) Driver Output Current vs. Input Voltage

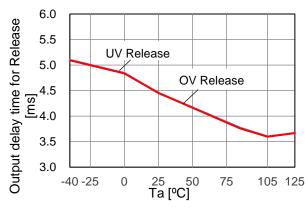


8) Driver Output Current vs. DOUT Pin Voltage $V_{SENSE} = 0 V$, Ta = 25°C



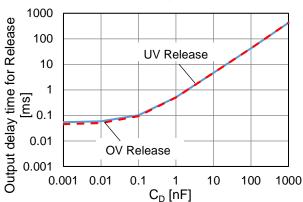
9) Release Delay Time vs. Temperature

 $V_{UVSET} = 3.3 \text{ V/V}_{OVSET} = 3.7 \text{ V}, V_{DD} = 14 \text{ V}, C_D = 10 \text{ nF}$ $V_{UVSET} = 3.3 \text{ V/V}_{OVSET} = 3.7 \text{ V}, V_{DD} = 14 \text{ V}, Ta = 25^{\circ}C$



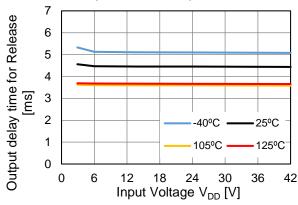
10) Release Delay Time vs.

External Capacitor for CD Pin

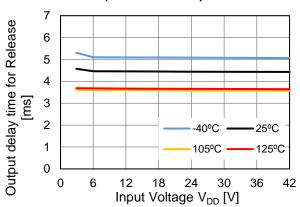


11) Release Delay Time vs. Input Voltage $C_D = 10 \text{ nF}$

 $V_{SENSE} = 0 V \rightarrow (V_{UVSET} + V_{OVSET}) / 2$

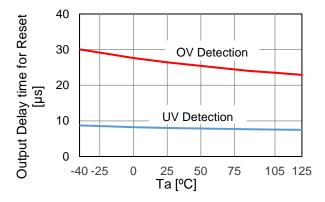


 $V_{SENSE} = 5.5 \text{ V} \rightarrow (V_{UVSET} + V_{OVSET}) / 2$

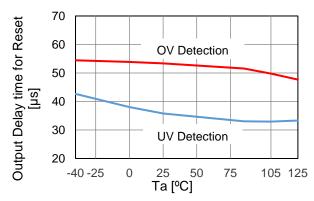


12) Detection Delay Time vs. Temperature V_{DD} = 14 V, V_{UVSET} = 3.3 V / V_{OVSET} = 3.7 V

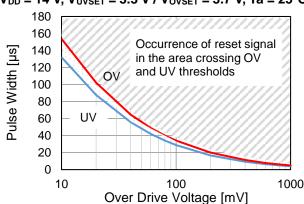
 V_{SENSE} = 3.5 V \rightarrow 0 V (UV), 3.5 V \rightarrow 5.5 V (OV)

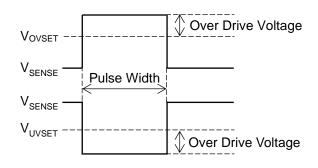


 V_{SENSE} = 3.5 V \rightarrow 3.2 V (UV), 3.5 V \rightarrow 3.81 V (OV)

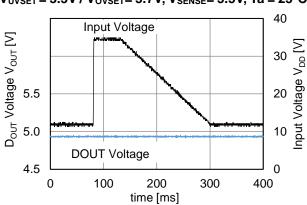


13) SENSE Pulse Width vs. Over Drive Voltage V_{DD} = 14 V, V_{UVSET} = 3.3 V / V_{OVSET} = 3.7 V, Ta = 25°C

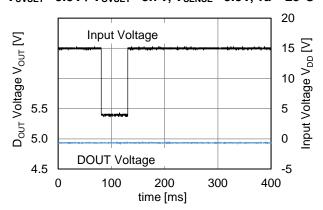




14) Load Dump V_{UVSET} = 3.3V / V_{OVSET} = 3.7V, V_{SENSE} = 3.5V, Ta = 25°C



15) Cranking V_{UVSET}= 3.3V / V_{OVSET}= 3.7V, V_{SENSE}= 3.5V, Ta = 25°C



PD-SOT-23-6-(125150)-JE-A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

Measurement Conditions

Item	Measurement Conditions			
Environment	Mounting on Board (Wind Velocity = 0 m/s)			
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)			
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm			
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square			
Through-holes	φ 0.3 mm × 7 pcs			

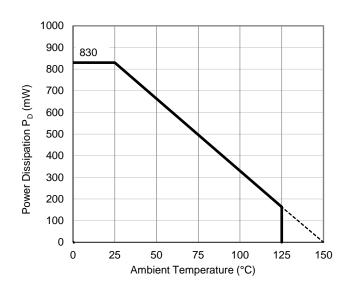
Measurement Result

 $(Ta = 25^{\circ}C, Tjmax = 150^{\circ}C)$

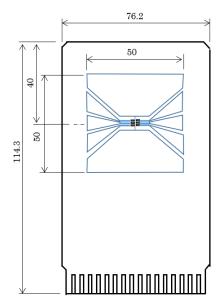
Item	Measurement Result
Power Dissipation	830 mW
Thermal Resistance (θja)	θja = 150°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 51°C/W

θja: Junction-to-Ambient Thermal Resistance

ψjt: Junction-to-Top Thermal Characterization Parameter

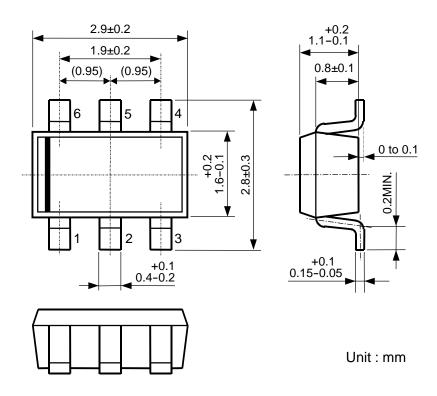


Power Dissipation vs. Ambient Temperature



Measurement Board Pattern

DM-SOT-23-6-JE-B



SOT-23-6 Package Dimensions (Unit: mm)



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